

Efficient interfacial charge transfer in CVD grown non-van der Waals $\text{Bi}_2\text{O}_2\text{Se}/\text{CsPbBr}_3$ type-I heterostructure for improved photodetection

Md Tarik Hossain¹

Mandira Das¹, Joydip Ghosh¹, Subhradip Ghosh¹, P K Giri^{1,2}

¹Department of Physics, Indian Institute of Technology Guwahati, Assam, India

²Centre for Nanotechnology, Indian Institute of Technology Guwahati, Assam, India

tarik@iitg.ac.in

Charge transfer in a 2D semiconductor heterostructure plays an important role in high-performance photodetectors and energy harvesting devices. Herein, we will discuss a series of experimental investigation of interfacial charge transfer in the $\text{Bi}_2\text{O}_2\text{Se}/\text{CsPbBr}_3$ (2D/0D) heterostructure through various microscopic and spectroscopic tools. We integrated the few-layer $\text{Bi}_2\text{O}_2\text{Se}$ nanosheet (2D) possessing superior electron mobility and CsPbBr_3 nanocrystals (0D) with high light-harvesting capability for efficient broadband photodetection. The band alignment reveals a type-I heterojunction, and the device under reverse bias reveals a fast response time of 12 $\mu\text{s}/24 \mu\text{s}$ (rise time/fall time) and an improved responsivity in the 390 to 840 nm range due to the effective interfacial charge transfer and efficient interlayer coupling at the $\text{Bi}_2\text{O}_2\text{Se}/\text{CsPbBr}_3$ interface. Notably, a photodetector with a peak responsivity of $\sim 10^3 \text{ A W}^{-1}$ was achieved in the $\text{Bi}_2\text{O}_2\text{Se}/\text{CsPbBr}_3$ heterostructure due to the synergistic effects in the heterostructure under ambient conditions. These results are significant for the development of non-van der Waals heterostructure based high-performance low-powered photodetectors.

References

[1] Hossain, M.T., et al., *Nanoscale*, 2021. 13(35): p. 14945-14959

Figures

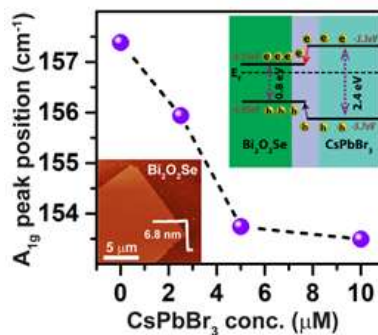


Figure 1: Evolution of characteristics Raman mode (A_{1g}) of $\text{Bi}_2\text{O}_2\text{Se}$ with the variation of CsPbBr_3 nanocrystals amount. Lower inset denotes Atomic force microscopy image of few layer $\text{Bi}_2\text{O}_2\text{Se}$ grown on mica. Upper Inset shows the energy band alignment between the $\text{Bi}_2\text{O}_2\text{Se}/\text{CsPbBr}_3$ heterostructure.

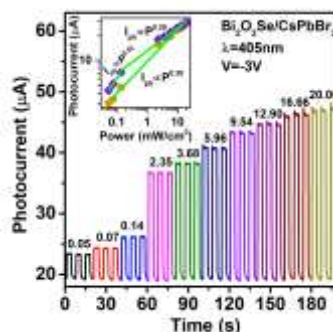


Figure 2: Photocurrent response as a function of the illumination intensity (ON/OFF) for the heterojunction photodetector. The inset shows the power-law fitting.